IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

Lynn Forester, et al

Docket: 30-3928 (4780) DIV-1

Serial Number: 10/726,154

Group Art Unit:

Filed: December 2, 2003

Examiner:

For: Electron-Beam Processed Films for Microelectronic Structures

DISCLOSURE UNDER 37 C.F.R. 1.56

Commissioner For Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

Submitted herewith on Form PTO-1449 is a listing of documents known to Applicant in order to comply with Applicant's duty of disclosure pursuant to 37 C.F.R. 1.56. Copies of the documents are also being submitted herewith to comply with the provisions of 37 C.F.R. 1.97 and 1.98.

The submission of these documents is not intended as an admission that any or all of these materials are prior art against the claims of the present application. Applicant does not waive any rights to file Affidavits under 37 C.F.R. 1.131, to copy claims from the listed patent documents, or to take any other action which would be appropriate in the event that one or more of the documents are determined to be questionable as references against the claims of the present application.

None of these documents are believed to impair the patentability of the presently claimed invention. Nevertheless, to complete the record, formal consideration and citation of these documents is requested.

Respectfully submitted,

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Date: February 9, 2004

I hereby certify that this document, including all attachments, is being deposited with the United States Postal Service "Express Mail-Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above in a postage paid envelope addressed to the Commissioner For Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

Richard S. Roberts

Reg. No. 27,941

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